

Schottky barrier diode

RB751S-40 / RB751V-40

●Applications

High speed switching
For Detection

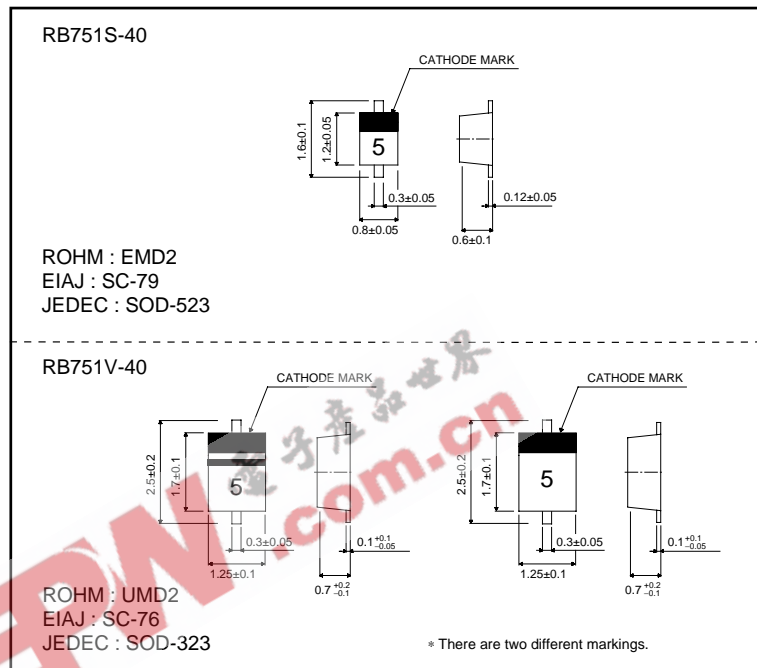
●Features

- 1) Small surface mounting type.
(EMD2, UMD2)
- 2) Low reverse current and low forward voltage.
- 3) High reliability.

●Construction

Silicon epitaxial planar

●External dimensions (Units : mm)



●Absolute maximum ratings (Ta = 25°C)

| Parameter | Symbol | Limits | Unit |
|-----------------------------|-----------|----------|------|
| Peak reverse voltage | V_{RM} | 40 | V |
| DC reverse voltage | V_R | 30 | V |
| Mean rectifying current | I_o | 30 | mA |
| Peak forward surge current* | I_{FSM} | 200 | mA |
| Junction temperature | T_j | 125 | °C |
| Storage temperature | T_{stg} | -40~+125 | °C |

* 60 Hz for 1 μ s

●Electrical characteristics (Ta = 25°C)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
|-------------------------------|--------|------|------|------|---------------|------------------------------------|
| Forward voltage | V_F | - | - | 0.37 | V | $I_F = 1\text{mA}$ |
| Reverse current | I_R | - | - | 0.5 | μA | $V_R = 30\text{V}$ |
| Capacitance between terminals | C_T | - | 2.0 | - | pF | $V_R = 1\text{V}, f = 1\text{MHz}$ |

Note) ESD sensitive product handling required.

Diodes

●Electrical characteristic curves (Ta = 25°C)

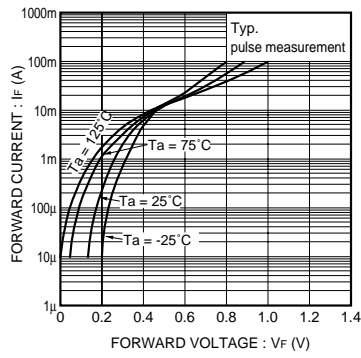


Fig. 1 Forward characteristics

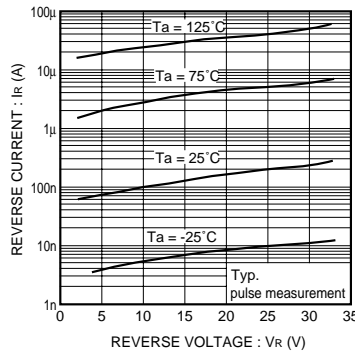


Fig. 2 Reverse characteristics

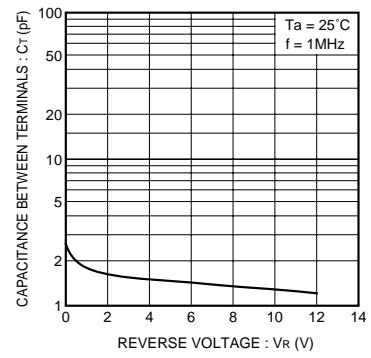


Fig. 3 Capacitance between terminals characteristics

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